

EAST Search History

(20 pp) 

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|--|--|------------------|---------|------------------|
| L1 | 1214 | sputtering near4 ("SnO.sub.2" "ZnO") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/23 13:11 |
| L2 | 211 | sputtering near4 ("SnO.sub.2" "ZnO") and channel and semiconductor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/23 13:11 |
| L3 | 4 | sputtering near4 ("SnO.sub.2" "ZnO") and channel and semiconductor and (Carcia.in. Cillessen.in.) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/23 13:55 |
| L4 | 1 | ("6,100,558").PN. | USPAT; USOCR | OR | OFF | 2007/11/23 14:41 |
| L5 | 13512 | ((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCLS. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/23 14:42 |
| L6 | 6 | 5 and (thin adj film adj transistor tft) and (zinc-tin-oxide Zn-Sn-oxide (ZnO near10 "SnO.sub.2") ("Zn.sub.2" near1 "SnO.sub.4") zinc adj stann?te "ZnSnO.sub.3") near20 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/23 14:46 |
| L7 | 3 | ((randy near2 hoffman).in. (hai near2 chiang).in. (john near2 wager).in. hewlett.as. oregon.as.) and (thin adj film adj transistor tft). clm. and (zinc-tin-oxide Zn-Sn-oxide (ZnO near10 "SnO.sub.2") ("Zn.sub.2" near1 "SnO.sub.4") zinc adj stann?te "ZnSnO.sub.3") near20 channel.clm. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/23 14:48 |

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| S1 | 3 | (("5,470,768") or ("5,879,973") or ("6,569,720")).PN. | USPAT; EPO; JPO; IBM_TDB | OR | OFF | 2006/05/31 15:33 |
| S2 | 20 | (("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550")).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/01 16:48 |
| S3 | 10 | (("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550")).PN. | US-PGPUB; USPAT | OR | OFF | 2005/10/01 16:53 |
| S4 | 1 | ("20030013261").PN. | US-PGPUB; USPAT | OR | OFF | 2005/10/01 16:52 |
| S5 | 11 | S3 S4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/01 16:53 |
| S6 | 9 | (("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462")).PN. or ((2002/0153587) or (2002/0171085)).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/10/01 16:56 |
| S7 | 11 | (("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085")).PN. | US-PGPUB; USPAT | OR | OFF | 2005/10/01 16:57 |
| S8 | 0 | ep-0040076\$-\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/01 16:58 |

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| S9 | 0 | ep-00040076\$-\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/01 16:59 |
| S10 | 82 | sasano.in. | EPO | OR | OFF | 2005/10/01 17:02 |
| S11 | 0 | sasano.in. and drain and compound | EPO | OR | OFF | 2005/10/01 17:01 |
| S12 | 0 | sasano.in. and drain | EPO | OR | OFF | 2005/10/01 17:02 |
| S13 | 4 | sasano.in. and semiconductor | EPO | OR | OFF | 2005/10/01 17:02 |
| S14 | 1 | (EP-40076-\$).did. | EPO | OR | OFF | 2005/10/01 17:08 |
| S15 | 4 | ((("5,744,864") or ("20020101557")). PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/01 17:08 |
| S16 | 2 | ((("5,744,864") or ("20020101557")). PN. | US-PGPUB; USPAT | OR | OFF | 2005/10/01 17:08 |
| S17 | 4 | "763353".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 11:40 |
| S18 | 4 | "763353".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 11:42 |
| S19 | 2 | "20040127038".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 11:51 |
| S20 | 5 | "2004023432".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 11:52 |
| S21 | 2 | "20040023432".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 11:53 |
| S22 | 4 | S19 S21 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 11:55 |

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| S23 | 2 | jp-2003086808\$-\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 11:56 |
| S24 | 2 | ("20030047785").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 11:56 |
| S25 | 0 | Garcia.in. and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 12:44 |
| S26 | 0 | ("257"/\$7.ccls. "438"/\$7.ccls. "117"/\$7.ccls.) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/31 12:45 |
| S27 | 3 | ("257"/\$7.ccls. "438"/\$7.ccls. "117"/\$7.ccls.) and (zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/31 12:48 |
| S28 | 10 | (zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/31 12:49 |
| S29 | 2 | (zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/31 12:50 |
| S30 | 0 | (zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 13:02 |
| S31 | 0 | (zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4" cubic adj spinel) near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 13:02 |

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| S32 | 0 | (zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4" zinc adj spinel) near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 13:10 |
| S33 | 324 | transparent near1 (thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 13:11 |
| S34 | 0 | (transparent near1 (thin adj film adj transistor tft) tft) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/31 13:12 |
| S35 | 0 | ((transparent near1 (thin adj film adj transistor tft)) tft) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/05/31 13:12 |
| S36 | 0 | alumin\$1um adj titanate near6 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/05/31 15:33 |
| S37 | 9707 | ("AlO.sub."\$4 "TiO.sub."\$4 "Al.sub."\$4 alumin\$1um adj titanate titanium adj aluminate) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 09:58 |
| S38 | 115 | ((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 10:00 |
| S39 | 79 | ((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad<"20030726" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 10:03 |

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| S40 | 0 | ((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) near15 gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad<"20030726" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 10:16 |
| S41 | 4 | "763353".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/01 11:39 |
| S42 | 706 | ((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near8 (titanium adj oxide ("Ti. sub."\$3 near1 (O "O.sub."\$3)) "TiO. sub."\$3) same gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 11:52 |
| S43 | 131 | ((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near8 (titanium adj oxide ("Ti. sub."\$3 near1 (O "O.sub."\$3)) "TiO. sub."\$3) near10 gate near10 (dielectric insulati\$2) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 11:53 |
| S44 | 66 | ((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near8 (titanium adj oxide ("Ti. sub."\$3 near1 (O "O.sub."\$3)) "TiO. sub."\$3) near10 gate near10 (dielectric insulati\$2) | USPAT | OR | ON | 2006/06/01 11:53 |
| S45 | 2 | "20050253157".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/01 15:47 |
| S46 | 140 | rf adj sputtering near6 amorphous | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/01 15:47 |
| S47 | 0 | (zno zinc adj oxide) near10 (rf adj sputtering near6 amorphous) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 15:48 |
| S48 | 16 | (oxide) near10 (rf adj sputtering near6 amorphous) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 15:50 |

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| S49 | 259 | (oxide) near10 (sputtering near6 amorphous) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 15:50 |
| S50 | 19 | (zinc adj oxide zno) near10 (sputtering near6 amorphous) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 15:51 |
| S51 | 1 | (US-20050017244-\$).did. | US-PGPUB | OR | OFF | 2006/06/01 16:10 |
| S52 | 1 | S51 and transparent | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 16:10 |
| S53 | 0 | dissocation adj constant near5 (zinc adj stannate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 16:17 |
| S54 | 0 | dissocation adj constant near5 ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") (zinc adj stannate)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 16:40 |
| S55 | 0 | (indium-tin-oxide indium adj tin adj oxide ITO) and "20040127038".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:16 |
| S56 | 11 | drain-to-gate near4 bias | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:24 |
| S57 | 1894 | drain near2 connecti\$2 near2 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:25 |
| S58 | 7956 | drain near1 connect\$3 near1 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:25 |

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| S59 | 571 | drain near1 connecti\$3 near1 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:33 |
| S60 | 49 | back adj gate and gate-to-drain | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:34 |
| S61 | 2 | back adj gate and gate-to-drain and (tft thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:35 |
| S62 | 2 | back adj gate and gate-to-drain and (otft tft thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:35 |
| S63 | 2 | (back adj gate back-gate) and gate-to-drain and (otft tft thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:36 |
| S64 | 334 | (back adj gate back-gate) and (otft tft thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 17:36 |
| S65 | 267 | (back adj gate back-gate) and (otft tft thin adj film adj transistor) and circuit | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 18:02 |
| S66 | 29 | hot adj electron.ti,ab,clm. and gate-to-drain | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 18:05 |
| S67 | 585 | hot adj electron.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 18:11 |
| S68 | 40 | hot adj electron adj effect.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 18:14 |

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| S69 | 18 | hot adj electron adj effect.ti. and gate near5 drain | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/01 18:15 |
| S70 | 1 | (US-20050017244-\$).did. | US-PGPUB | OR | OFF | 2006/06/02 08:40 |
| S71 | 0 | S70 and means | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 08:41 |
| S72 | 1 | (US-20050017244-\$).did. | US-PGPUB | OR | OFF | 2006/06/02 08:41 |
| S73 | 0 | S70 and "means" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 08:41 |
| S74 | 524 | (thin adj film adj transistor tft).ti,ab, clm. and (indium-tin ITO) near8 source and (indium-tin ITO) near8 drain | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 09:41 |
| S75 | 54 | (thin adj film adj transistor tft).ti,ab, clm. and (indium-tin ITO) near2 source and (indium-tin ITO) near2 drain | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 09:41 |

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| S76 | 41 | (US-20050104508-\$ or US-20040066484-\$ or US-20030185266-\$ or US-20050017244-\$ or US-20030207502-\$ or US-20030224550-\$ or US-20030219530-\$ or US-20030218222-\$ or US-20030218221-\$ or US-20030186489-\$ or US-20030139026-\$ or US-20030104659-\$ or US-20030180996-\$ or US-20030013261-\$ or US-20020171085-\$ or US-20020153587-\$ or US-20040127038-\$ or US-20040023432-\$ or US-20030047785-\$).did. or (US-4521698-\$ or US-6569720-\$ or US-6561174-\$ or US-6391462-\$ or US-6362499-\$ or US-5744864-\$ or US-5107314-\$ or US-4887255-\$ or US-4589026-\$ or US-5879973-\$ or US-5470768-\$ or US-6255655-\$ or US-6255130-\$ or US-4559238-\$ or US-6653206-\$ or US-6617609-\$ or US-7017830-\$).did. or (EP-40076-\$).did. or (JP-2003086808-\$).did. or (WO-200217368-\$ or WO-2004034449-\$ or US-20030047785-\$).did. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2006/06/02 10:16 |
| S77 | 0 | ((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) near15 gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad<"20030726" and S76 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 10:17 |
| S78 | 0 | ("AlO.sub."\$3 "A.sub.2O.sub.3") near10 ("TiO.sub."\$72 "TiO.sub.2") near10 ((insulati\$2 dielectric) near2 gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 10:25 |
| S79 | 69580 | ("Al.sub."\$1 near1 "O.sub."\$1) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 10:26 |

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| S80 | 0 | ("Al.sub."\$1 near1 "O.sub."\$1) near20 ("Ti.sub."\$1 near1 "O.sub." \$1) near20 gate near20 (dielectric insulati\$2) near20 (combination multi-layer\$2 multilayer\$2) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 10:28 |
| S81 | 0 | ("Al.sub."\$1 near1 "O.sub."\$1) near20 ("Ti.sub."\$1 near1 "O.sub." \$1) near20 gate near20 (dielectric insulati\$2) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 10:28 |
| S82 | 87 | ((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 10:30 |
| S83 | 0 | ((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 mixture | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 10:30 |
| S84 | 1 | ((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 mixture | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 10:35 |
| S85 | 9 | ((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 10:42 |
| S86 | 0 | ((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer) and (thin adj film adj transistor tft otft) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 10:43 |
| S87 | 9 | ((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 10:53 |

EAST Search History

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|-----|------|--|---|----|----|------------------|
| S88 | 9 | ((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1 (alumin\$1um adj titanate) (titanium adj aluminate)) near20 ((("Ti.sub."\$1 near1 "O.sub." "\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 10:55 |
| S89 | 9 | ((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3 (alumin\$1um adj titanate) (titanium adj aluminate)) near20 ((("Ti.sub."\$3 near1 "O.sub." "\$3) "TiO.sub."\$3) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 12:48 |
| S90 | 209 | ((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 ((("Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 barrier | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 12:49 |
| S91 | 5 | ((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 ((("Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 barrier near20 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 12:52 |
| S92 | 0 | ((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 (cap adj (layer film)) near20 gate near20 (semiconductor channel) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 12:53 |
| S93 | 3 | ((alumin\$1um adj oxide) ("Al.sub." "\$3 near1 (O "O.sub."\$3)) "AlO.sub." "\$3) near8 (cap adj layer) near20 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 12:59 |
| S94 | 1839 | ((alumin\$1um adj oxide) ("Al.sub." "\$3 near1 (O "O.sub."\$3)) "AlO.sub." "\$3) near4 barrier | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 12:59 |
| S95 | 45 | ((alumin\$1um adj oxide) ("Al.sub." "\$3 near1 (O "O.sub."\$3)) "AlO.sub." "\$3) near4 barrier near4 (Ti titanium) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 13:03 |
| S96 | 27 | ((alumin\$1um adj oxide) ("Al.sub." "\$3 near1 (O "O.sub."\$3)) "AlO.sub." "\$3) near4 barrier near4 (Ti titanium) and gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 13:03 |

EAST Search History

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|----------|-------|--|---|----|-----|------------------|
| S97 | 11320 | ((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 14:32 |
| S98 | 0 | S97 and ((alumin\$1um adj titanate) (titanium adj aluminate) ("Al.sub.\$2 near1 "O.sub.\$2 "AlO.sub.\$2 alumin\$1um adj oxide)) near20 ("Ti.sub.\$2 near1 "O.sub.\$2 near1 "TiO.sub.\$2 (titanium adj oxide)) near20 gate and (channel semiconductor) near4 (("Zn.sub.\$2 near1 "SnO.sub.\$2) (("Zn.sub.\$2 near1 "O") near10 ("SnO.sub.\$2))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 14:47 |
| S99 | 8 | ((("6836540") or ("6998656") or ("6940097") or ("7026713")).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 14:49 |
| S10 0 | 45 | randy near1 hoffman.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/06/02 14:49 |
| S10 1 | 26 | randy near1 hoffman.in. and (zinc adj oxide ZnO ("Zn.sub.2" near1 "O")) and (Ti titanium) and (Al alumin\$1um) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/06/02 14:51 |
| S10 2 | 89 | (hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/07/14 11:09 |
| S10 3 | 2 | (hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti,ab,clm. and stannate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/07/14 11:10 |
| S10 4 | 18 | (hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti,ab,clm. and (stannate "SnO.sub.\$2) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/07/14 11:10 |

EAST Search History

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| S10 5 | 2 | "20040127038".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/07/14 12:05 |
| S10 6 | 1 | (US-20050017244-\$).did. | US-PGPUB | OR | OFF | 2007/11/14 15:31 |
| S10 7 | 0 | (US-20050017244-\$).did. and means | US-PGPUB | OR | ON | 2007/11/14 15:31 |
| S10 8 | 1743 | (aluminum adj oxide) and strontium adj oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/14 19:15 |
| S10 9 | 7 | "410830".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/15 10:27 |
| S11 0 | 2 | ("20040127038").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/15 13:26 |
| S11 1 | 0 | ("533453.ap.").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/15 14:15 |
| S11 2 | 2 | ("20020172317").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/15 14:18 |
| S11 3 | 2 | ("4093886").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/15 14:53 |
| S11 4 | 0 | wo-9108180\$-\$\$.did. | USPAT | OR | OFF | 2007/11/15 14:54 |

EAST Search History

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|----------|----|--|--|----|-----|------------------|
| S11 5 | 2 | wo-9108180\$-\$.did. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/15 16:23 |
| S11 6 | 32 | percentage near3 porosity near3 "%" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/15 16:24 |
| S12 2 | 2 | "20040127038".pn. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/21 10:03 |
| S12 3 | 2 | "4521698".PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/21 10:05 |
| S12 4 | 2 | "6674495".PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/21 10:05 |
| S12 5 | 13 | "6100558" | USPAT | OR | OFF | 2007/11/21 10:50 |
| S12 6 | 1 | ("6100558").PN. | USPAT; USOCR | OR | OFF | 2007/11/21 10:52 |
| S12 7 | 2 | ("20040169210").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/21 10:53 |

EAST Search History

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|----------|----|---|--|----|-----|------------------|
| S12 8 | 2 | ("6184946").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/21 10:53 |
| S12 9 | 0 | ("20060183274").PN. | USPAT; USOCR | OR | OFF | 2007/11/22 08:36 |
| S13 0 | 9 | carcia.in. and thin adj film adj transistor | US-PGPUB; USPAT | OR | ON | 2007/11/22 08:44 |
| S13 1 | 6 | thin adj film adj transistor and (zinc-tin adj oxide zto) near4 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 08:49 |
| S13 2 | 7 | (tft thin adj film adj transistor) and (zinc-tin adj oxide zto) near8 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 08:50 |
| S13 3 | 11 | (tft thin adj film adj transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 08:52 |
| S13 4 | 12 | (tft thin adj film adj transistor mos mosfet) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 08:53 |
| S13 5 | 10 | (mos mosfet) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 08:53 |

EAST Search History

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|----------|-------|--|--|----|-----|------------------|
| S13 6 | 11 | (mosfet transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 08:56 |
| S13 7 | 11 | (mosfet transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide "zno:sn") near8 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 09:03 |
| S13 8 | 0 | ("20050017244").PN. | USPAT; USOCR | OR | OFF | 2007/11/22 09:03 |
| S13 9 | 2 | ("20050017244").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/22 09:06 |
| S14 0 | 2 | "20060284171" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/22 09:11 |
| S14 1 | 10 | zinc near1 tin near1 oxide near10 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/22 09:12 |
| S14 2 | 2 | zinc near1 tin near1 oxide near10 channel not hoffman.in. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 09:32 |
| S14 3 | 12023 | zinc near2 tin near2 oxide zito zto "zno:sn" "sno"\$3"zn" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 09:33 |

EAST Search History

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|----------|----|---|--|----|----|------------------|
| S14 4 | 26 | (zinc near2 tin near2 oxide zito zto "zno:sn" "sno"\$3"zn") near4 channel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 09:44 |
| S14 5 | 0 | zno near4 sno\$1 near4 (mixture combination) near10 channel and transistor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 09:45 |
| S14 6 | 0 | zno near4 sno\$1 near8 (mixture combination) near10 channel and transistor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 09:45 |
| S14 7 | 5 | (zinc adj oxide zno) near4 (tin adj oxide sno\$1) near8 (mixture combination) near10 channel and transistor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 09:50 |
| S14 8 | 31 | (zinc adj oxide zno) near4 (tin adj oxide sno\$1) near10 channel and transistor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 09:59 |
| S14 9 | 1 | (zinc-tin- adj oxide zinc adj tin adj oxide) near20 channel.clm. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 10:03 |
| S15 0 | 2 | "20040023432".pn. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 10:07 |

EAST Search History

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|----------|----|--|--|----|-----|------------------|
| S15 1 | 2 | jp-2003088808\$-\$.did. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 10:10 |
| S15 2 | 0 | ohtomo.in. and zto | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 10:11 |
| S15 3 | 0 | ohtomo.in. and (zinc-tin-oxide zto) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 10:11 |
| S15 4 | 0 | (ohtomo.in. kawasaki.in.) and (zinc-tin-oxide zto) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 10:17 |
| S15 5 | 23 | "5470788" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/22 10:18 |
| S15 6 | 3 | ((("5470788") or ("5879973") or ("6569720"))).PN. | USPAT; USOCR | OR | OFF | 2007/11/22 10:24 |
| S15 7 | 3 | ((("5470768") or ("5879973") or ("6569720"))).PN. | USPAT; USOCR | OR | OFF | 2007/11/22 10:30 |
| S15 8 | 11 | ((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085"))).PN. | US-PGPUB; USPAT | OR | OFF | 2007/11/22 10:31 |

EAST Search History

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|----------|-------|---|--|----|-----|------------------|
| S15 9 | 2 | ("20040127038").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/11/23 13:10 |
| S16 0 | 13987 | "SnO.sub.2" | USPAT | OR | OFF | 2007/11/23 07:02 |
| S16 1 | 0 | "SnO.sub.2" near10 "ZnO" near10 (combination mixture) near20 channel and transistor | USPAT | OR | ON | 2007/11/23 07:03 |
| S16 2 | 4 | "SnO.sub.2" near10 "ZnO" near10 (combination mixture) same channel and transistor | USPAT | OR | ON | 2007/11/23 08:41 |
| S16 3 | 2 | jp-60198861\$-\$\$.did. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/11/23 08:41 |